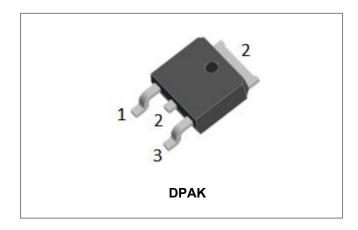


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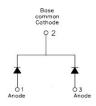
MBRD660CTL SCHOTTKY RECTIFIER



Features

- 125°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- "-A" is an AEC-Q101 qualified device
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	-	60	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =85°C, rectangular wave form	3(peg leg) 6(peg device)	A
Peak One Cycle Non-Repetitive Surge Current(peg leg)	I _{FSM}	8.3 ms, half Sine pulse	150	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V _{F1}	@ 3A, Pulse, T _J = 25 °C	0.48	0.50	V
(per leg) *	V _{F2}	@ 3A, Pulse, T _J = 125°C	0.43	0.45	V
Reverse Current (per leg) *	I _{R1}	$@V_R = \text{rated } V_{R,} T_J = 25 ^{\circ}\text{C}$	0.1	1	mA
	I _{R2}	$@V_R = \text{rated } V_{R,} T_J = 125 ^{\circ}\text{C}$	20	25	mA
Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	200	250	pF

^{*} Pulse width < 300 µs, duty cycle < 2%



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Junction Capacitance (PF)

10

0

5

10





Thermal-Mechanical Specifications:

Ratings and Characteristics Curves

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +125	°C
Storage Temperature	T _{stg}	-	-55 to + 125	°C
Typical Thermal Resistance Junction to Case	R _θ JC	-	6	°C/W
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

10000 1000 TJ=25°C

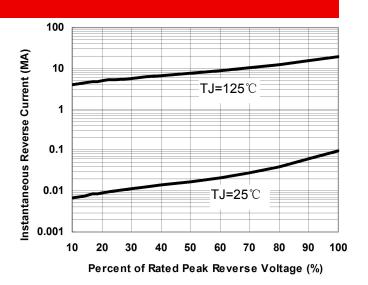


Fig.1-Typical Junction Capacitance

20

Reverse Voltage (V)

15

25

30

40

35



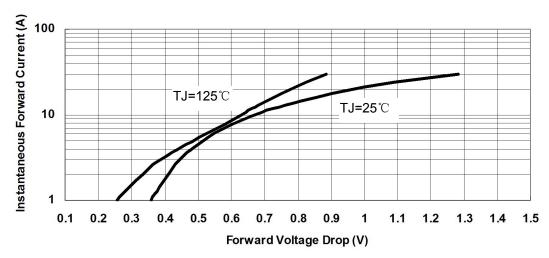


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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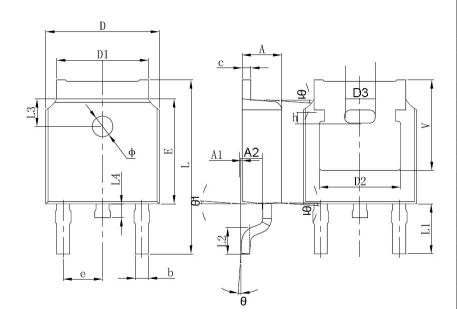


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Mechanical Dimensions DPAK



CVMDOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
Α	2.20	2.40	0.087	0.094	
A1	0.00	0.127	0.000	0.005	
b	0.66	0.86	0.026	0.034	
С	0.46	0.60	0.018	0.024	
D	6.50	6.70	0.256	0.264	
D1	5.13	5.46	0.202	0.215	
D2	4.83	REF.	0.190 REF.		
E	6.00	6.20	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.70	10.40	0.381	0.409	
L1	2.90 REF.		0.144 REF.		
L2	1.40	1.70	0.055	0.067	
L3	1.60 REF.		0.063 REF.		
L4	0.60	1.00	0.024	0.039	
Ф	1.10	1.30	0.043	0.051	
Θ	0°	8°	0°	8°	
h	0.00	0.30	0.000	0.012	
V	5.35 REF.		0.211	REF.	

Ordering Information

Device	Package	Shipping
MBRD660CTL	DPAK (Pb-Free)	2500pcs / reel
MBRD660CTLTR	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

Marking Diagram



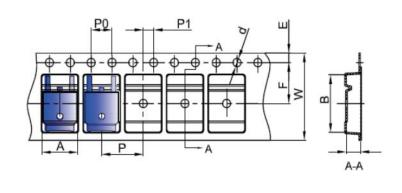
Where XXXXX is YYWWL

= Device Type MBR = Package type D = Forward Current (6A) 6 = Reverse Voltage (60V) 60 CTL = Configuration SSG = SSG = Year WW = Week = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Carrier Tape Specification DPAK



SYMBOL	Millimeters		
STWIDOL	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
C	2.60	2.80	
d	Ф1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

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MBRD660CTL



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